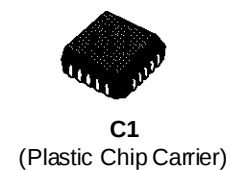
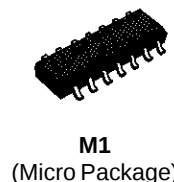
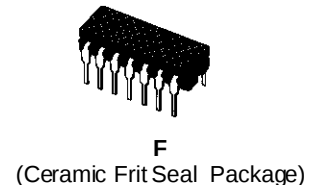
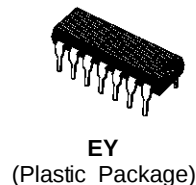


QUAD 2-INPUT NAND SCHMIDT TRIGGERS

- SCHMITT-TRIGGER ACTION ON EACH INPUT WITH NO EXTERNAL COMPONENTS
- HYSTERESIS VOLTAGE TYPICALLY 0.9V AT $V_{DD} = 5V$ AND 2.3V AT $V_{DD} = 10V$
- NOISE IMMUNITY GREATER THAN 50% OF V_{DD} (typ.)
- NO LIMIT ON INPUT RISE AND FALL TIMES
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



ORDER CODES :

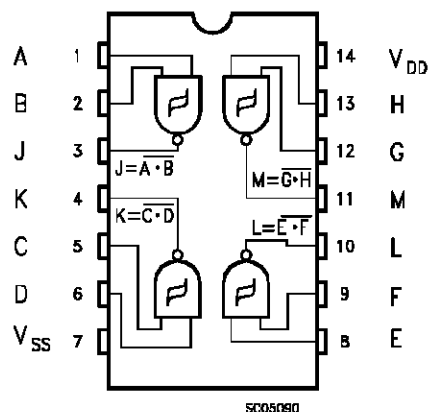
HCC4093BF	HCF4093BM1
HCF4093BEY	HCF4093BC1

DESCRIPTION

The **HCC4093B** (extended temperature range) and **HCF4093B** (intermediate temperature range) are available in 14-lead dual in-line plastic or ceramic package and plastic micropackage. The **HCC/HCF4093B** consists of four Schmitt-trigger circuits. Each circuit functions as a two-input NAND gate with Schmitt-trigger action on both inputs. The gate switches at different points for positive and negative-going signals.

The difference between the positive voltage (V_P) and the negative voltage (V_N) is defined as hysteresis voltage (V_H) (see fig. 1).

PIN CONNECTIONS



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		1		0.02	1		30	μA
			0/10			10		2		0.02	2		60	
			0/15			15		4		0.02	4		120	
			0/20			20		20		0.04	20		600	
		HCF Types	0/ 5			5		4		0.02	4		30	
			0/10			10		8		0.02	8		60	
			0/15			15		16		0.02	16		120	
V _P	Positive Trigger Threshold Voltage	a			5	2.2	3.6	2.2	2.9	3.6	2.2	3.6	V	
		a			10	4.6	7.1	4.6	5.9	7.1	4.6	7.1		
		a			15	6.8	10.8	6.8	8.8	10.8	6.8	10.8		
		b			5	2.6	4	2.6	3.3	4	2.6	4		
		b			10	5.6	8.2	5.6	7	8.2	5.6	8.2		
		b			15	6.3	12.7	6.3	9.4	12.7	6.3	12.7		
V _N	Negative Trigger Threshold Voltage	a			5	0.9	2.8	0.9	1.9	2.8	0.9	2.8	V	
		a			10	2.5	5.2	2.5	3.9	5.2	2.5	5.2		
		a			15	4	7.4	4	5.8	7.4	4	7.4		
		b			5	1.4	3.2	1.4	2.3	3.2	1.4	3.2		
		b			10	3.4	6.6	3.4	5.1	6.6	3.4	6.6		
		b			15	4.8	9.6	4.8	7.3	9.6	4.8	9.6		
V _H	Hysteresis Voltage	a			5	0.3	1.6	0.3	0.9	1.6	0.3	1.6	V	
		a			10	1.2	3.4	1.2	2.3	3.4	1.2	3.4		
		a			15	1.6	5	1.6	3.5	5	1.6	5		
		b			5	0.3	1.6	0.3	0.9	1.6	0.3	1.6		
		b			10	1.2	3.4	1.2	2.3	3.4	1.2	3.4		
		b			15	1.6	5	1.6	3.5	5	1.6	5		
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	− 2		− 1.6	− 3.2		− 1.15		mA
			0/ 5	4.6		5	− 0.64		− 0.51	− 1		− 0.36		
			0/10	9.5		10	− 1.6		− 1.3	− 2.6		− 0.9		
			0/15	13.5		15	− 4.2		− 3.4	− 6.8		− 2.4		
		HCF Types	0/ 5	2.5		5	− 1.53		− 1.36	− 3.2		− 1.1		
			0/ 5	4.6		5	− 0.52		− 0.44	− 1		− 0.36		
			0/10	9.5		10	− 1.3		− 1.1	− 2.6		− 0.9		
			0/15	13.5		15	− 3.6		− 3.0	− 6.8		− 2.4		

a : input on terminals 1, 5, 8, 12 or 2, 6, 9, 13 ; other inputs to V_{DD}.b : input on terminals 1 and 2, 5 and 6, 8 and 9, or 12 and 13 ; other inputs to V_{DD}.* T_{Low} = -55°C for **HCC** device : -40°C for **HCF** device.* T_{High} = +125°C for **HCC** device : +85°C for **HCF** device.

STATIC ELECTRICAL CHARACTERISTICS (continued)

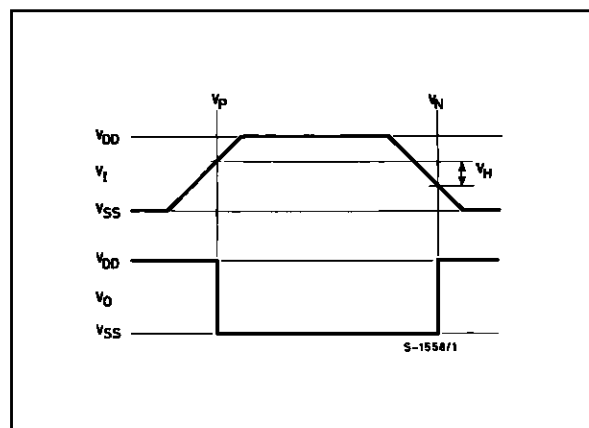
Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _{OL}	Output Sink Current		0/ 5	0.4		5	0.64		0.51	1		0.36		mA
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
			0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		± 0.1		± 10 ⁻⁵	± 0.1		± 1	μA	
		HCF Types	0/15		15		± 0.3		± 10 ⁻⁵	± 0.3		± 1		
C _I	Input Capacitance			Any Input					5	7.5			pF	

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^\circ C$, $C_L = 50pF$, $R_L = 200k\Omega$, typical temperature coefficient for all $V_{DD} = 0.3\%/^\circ C$ values , all input rise and fall time = 20ns)

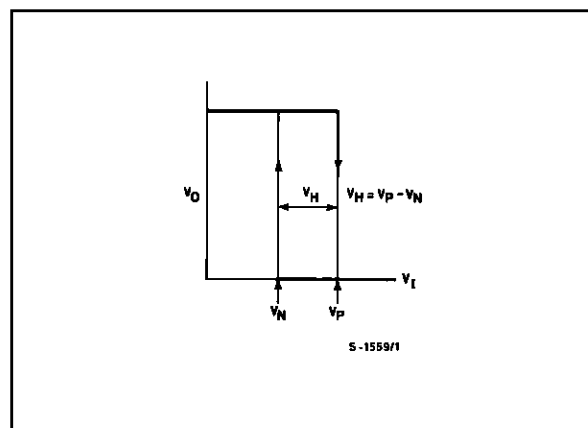
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH}, t_{PHL}	Propagation Delay Time		5		190	380	ns
			10		90	180	
			15		65	130	
t_{TLH}, t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

Figure1 : Hysteresis Definition, Characteristics and Test Setup.

(a) Definition of V_P , V_N and V_H



(b) Transfer characteristics of 1 of 4 gates



(c) Test setup

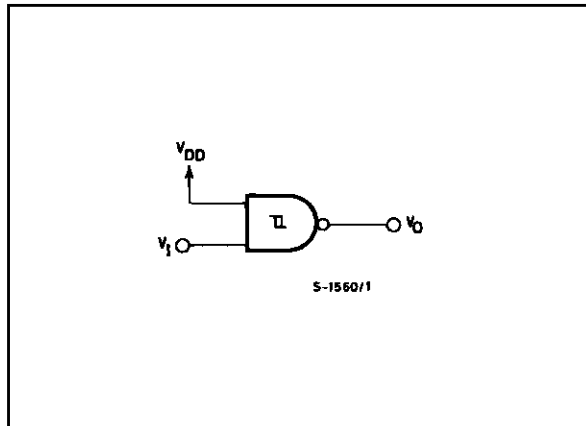


Figure 2 : Input and Output Characteristics.

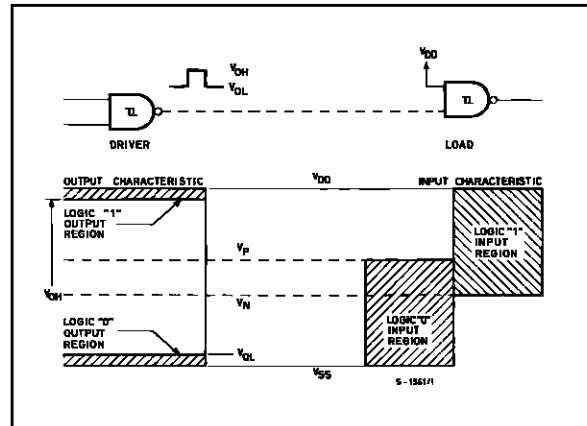


Figure 3 : Typical Current and Voltage Transfer Characteristics.

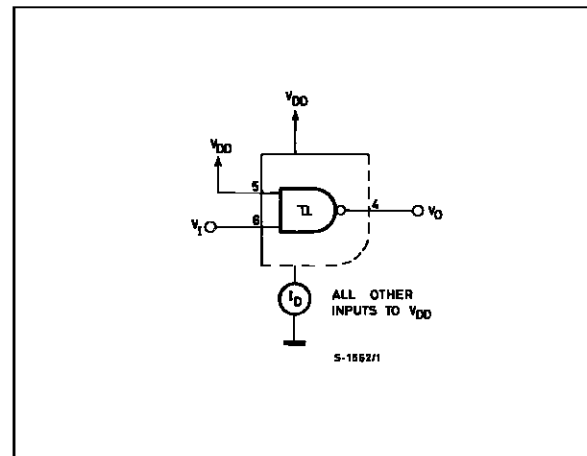
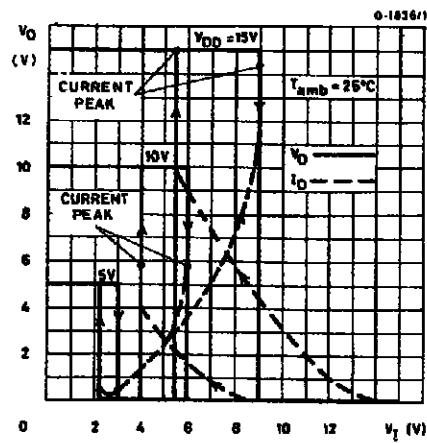


Figure 4 : Typical Voltage Transfer Characteristics as a Function of Temperature, and Test Circuit.

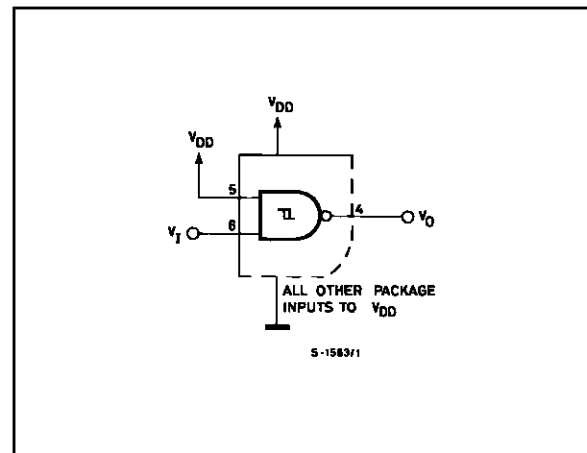
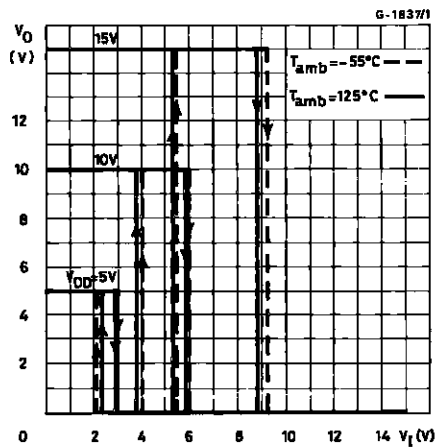


Figure 5 : Typical Output Low (sink) Current Characteristics.

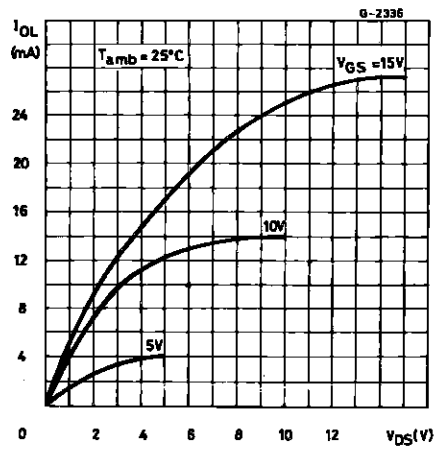


Figure 6 : Minimum Output Low (sink) Current Characteristics.

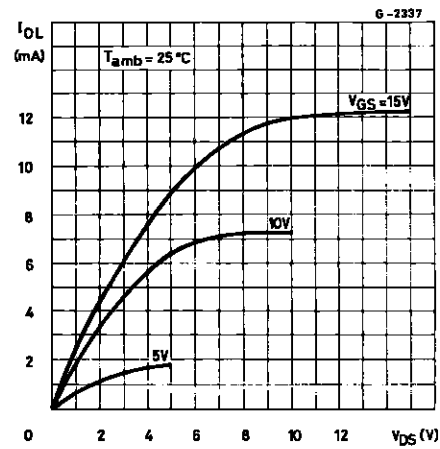


Figure 7 : Typical Output High (source) Current Characteristic.

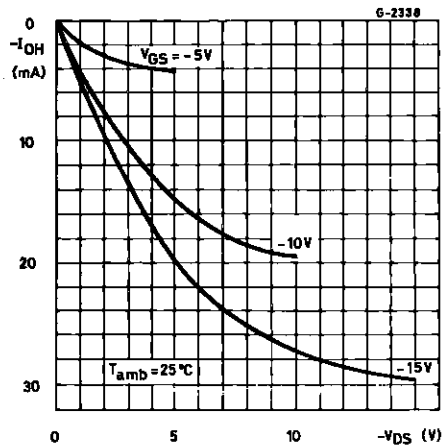


Figure 8 : Minimum Output High Current Characteristics.

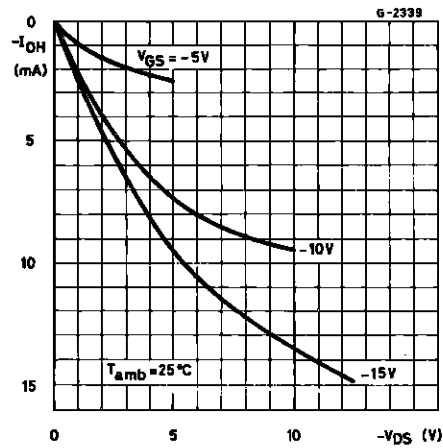


Figure 9 : Typical Propagation Delay Time vs. Supply Voltage.

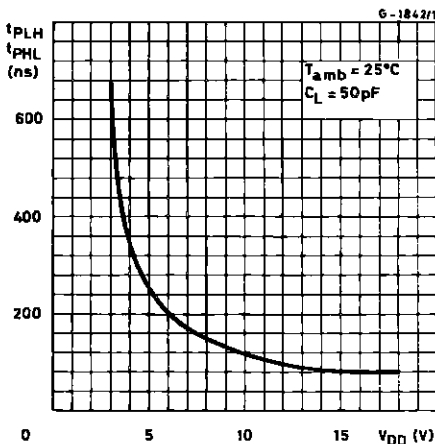


Figure 10 : Typical Transition Time vs. Load Capacitance.

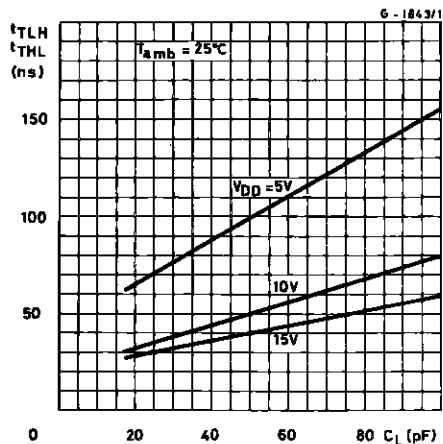


Figure 11 : Typical Trigger Threshold Voltage vs. V_{DD}

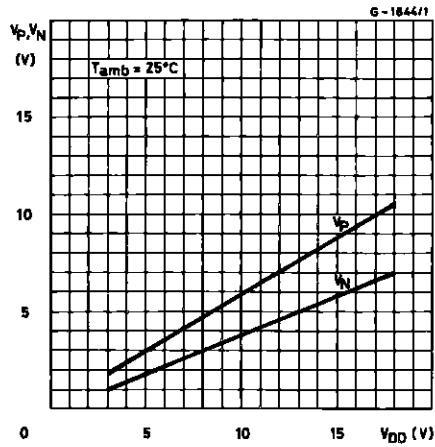


Figure 12 : Typical per cent Hysteresis vs. Supply Voltage.

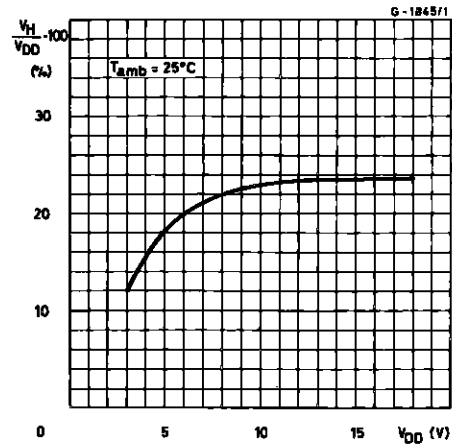


Figure 13 : Typical Dissipation Characteristics.

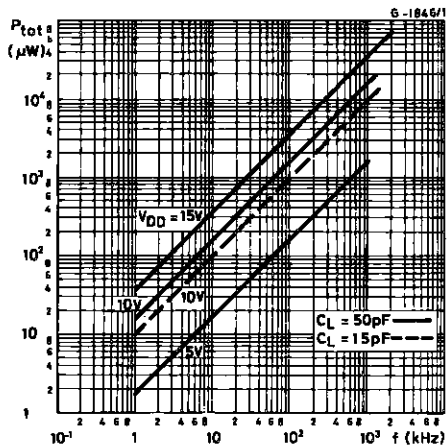
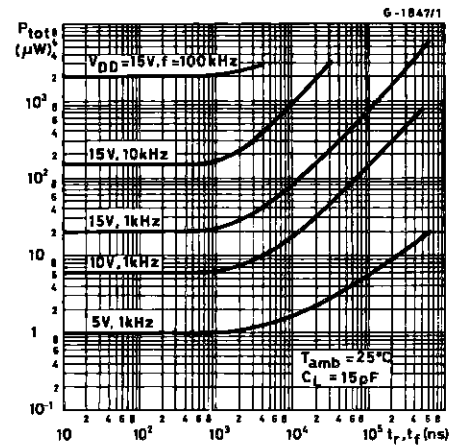


Figure 14 : Power Dissipation vs. Rise and Fall Times.



APPLICATIONS

Figure 15 : Wave Shaper.

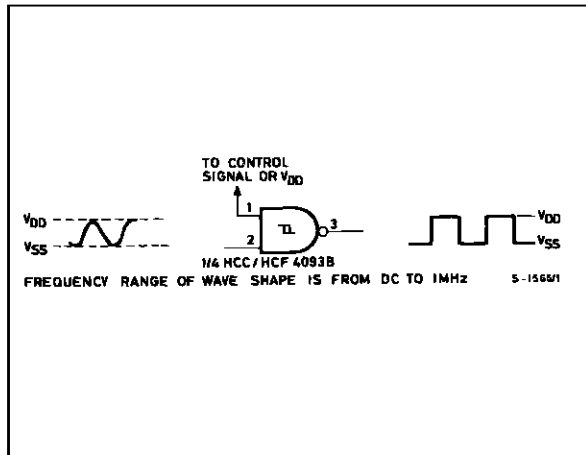


Figure 16 : Monostable Multivibrator.

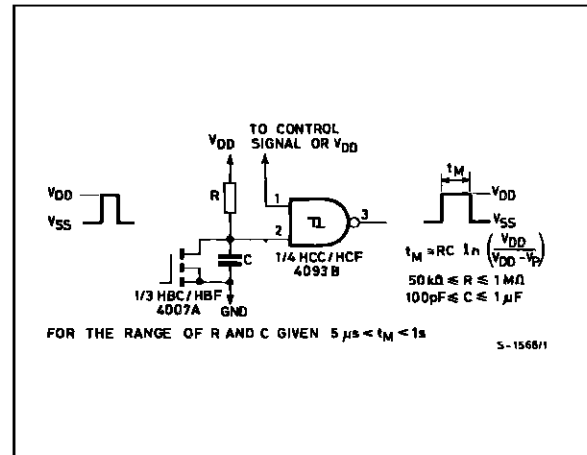
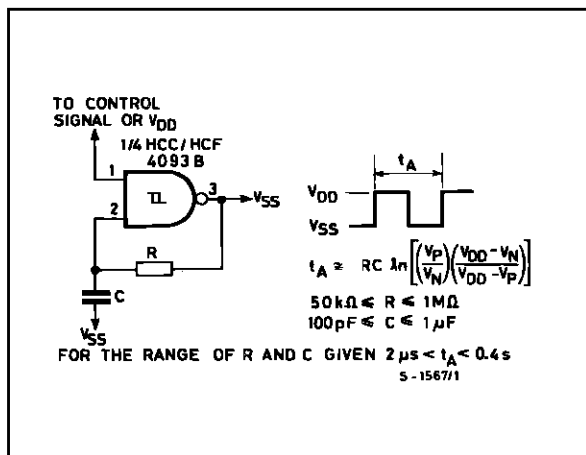


Figure17 : Astable Multivibrator.



TEST CIRCUITS

Figure18 : Quiescent Device Current.

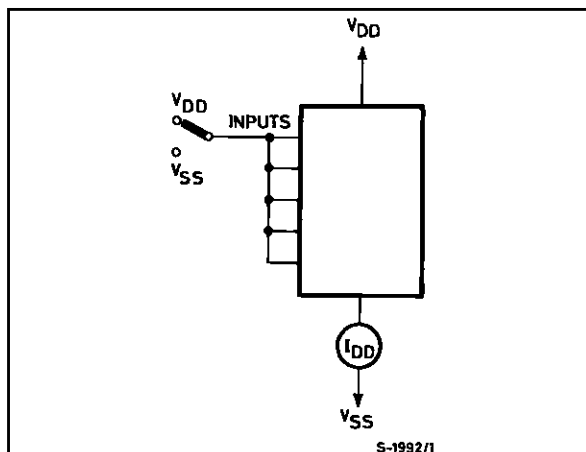
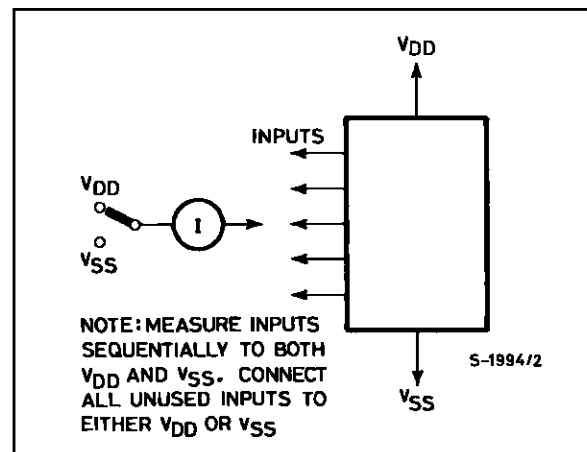
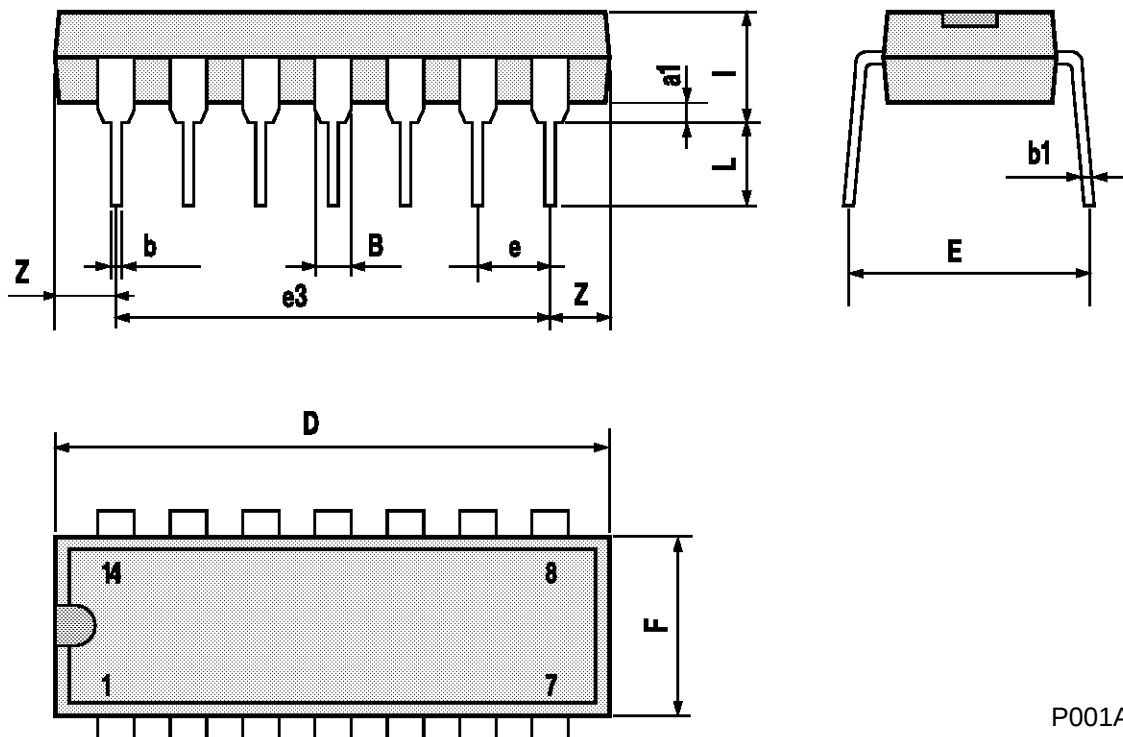


Figure 19 : Input Leakage Current.



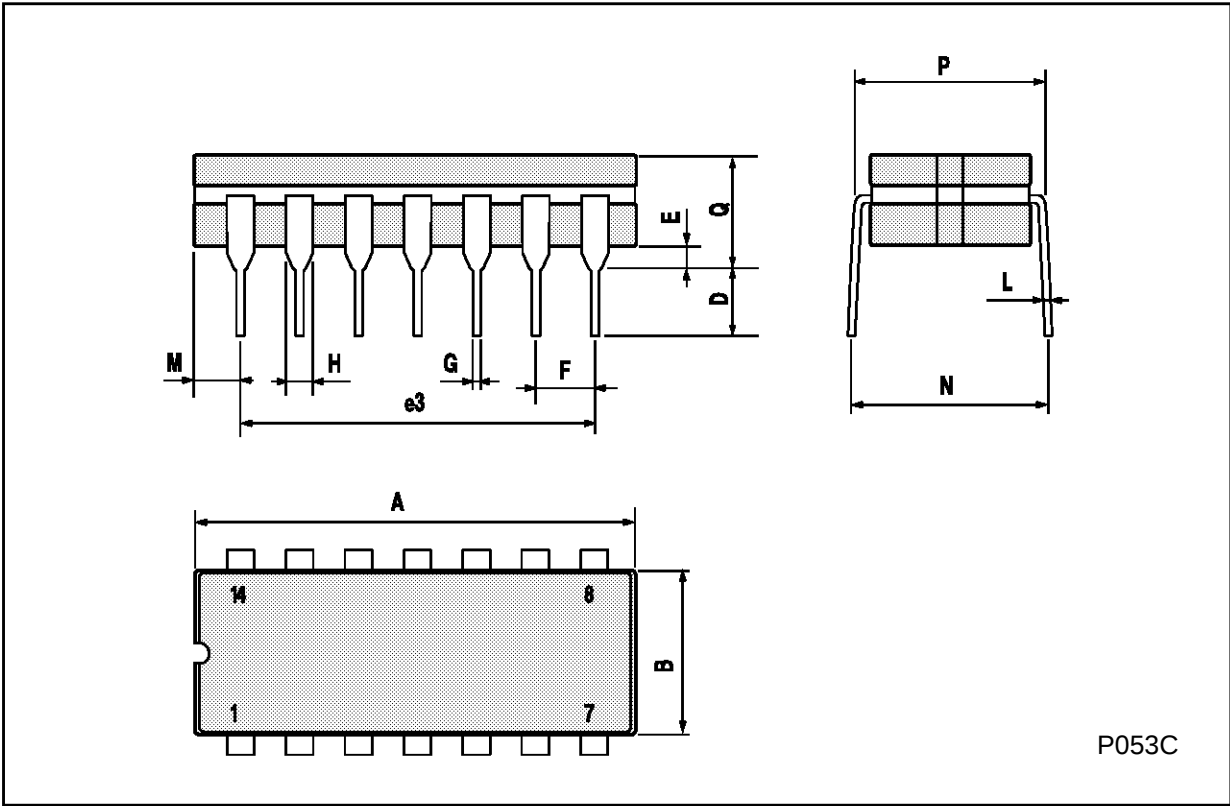
Plastic DIP14 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



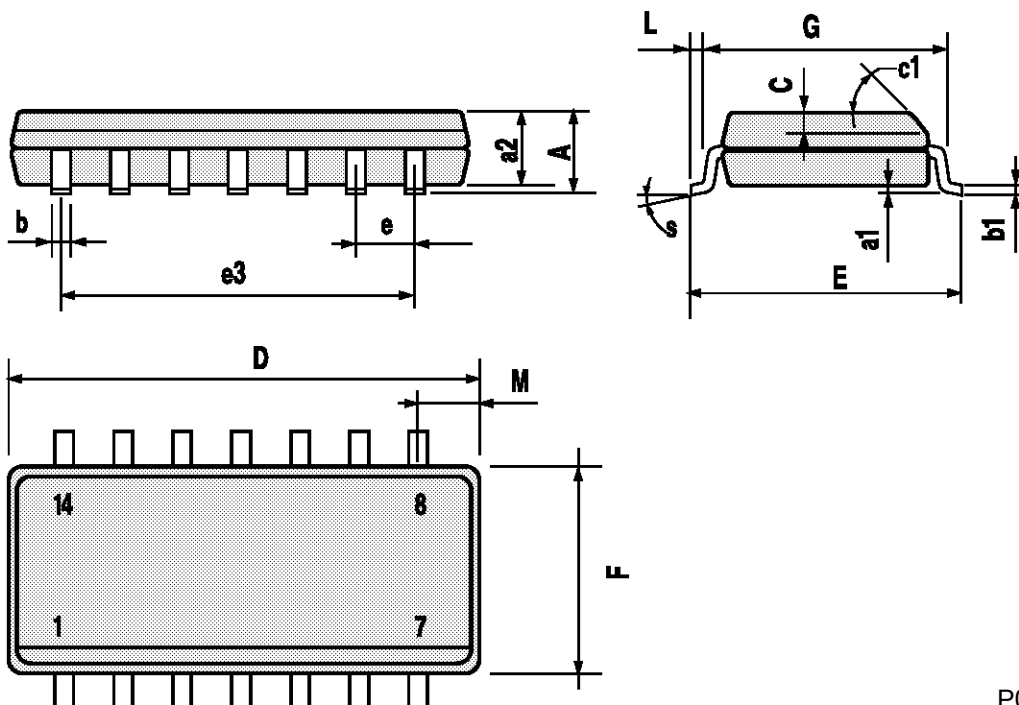
Ceramic DIP14/1 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7.0			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		15.24			0.600	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	1.52		2.54	0.060		0.100
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



SO14 MECHANICAL DATA

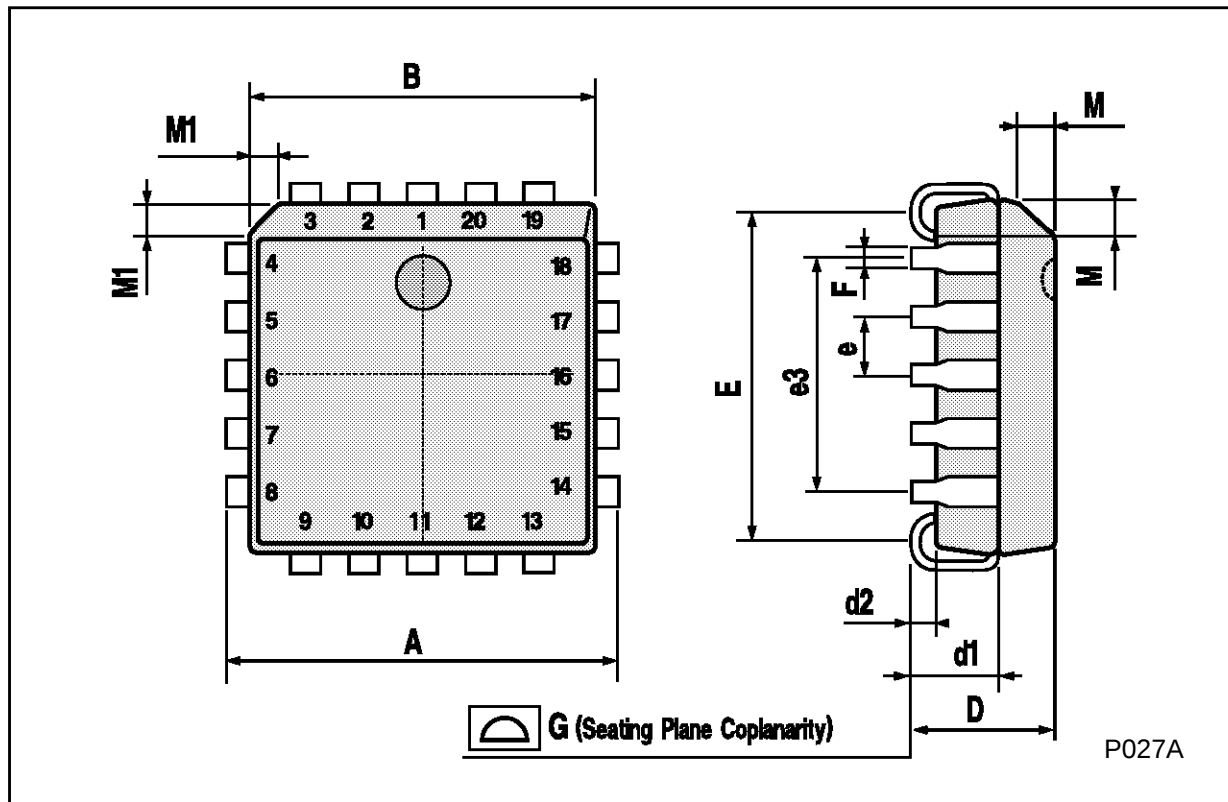
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



P013G

PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



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